



N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _C = +25 ℃	
30V	$8.5m\Omega$ @ $V_{GS} = 10V$	30A	
30 V	$10.5 m\Omega$ @ $V_{GS} = 4.5 V$	25A	

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

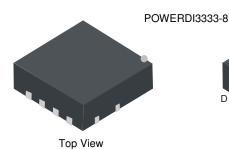
- Backlighting
- DC-DC Converters
- Power Management Functions

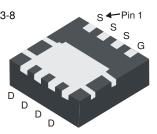
Features

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- 100% Rg tested
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

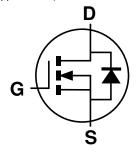
Mechanical Data

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)





Bottom View



Equivalent Circuit

Ordering Information (Note 4)

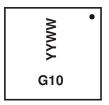
Part Number	Compliance	Case	Packaging
DMN3010LFG-7	Standard	POWERDI3333-8	2,000/Tape & Reel
DMN3010LFG-13	Standard	POWERDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

PowerDI3333-8



G10 = Product Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 for 2015) WW = Week Code (01 – 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteris	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Dusin Comment (Nata C) V 40V	Steady State	T _A = +25 °C T _A = +70 °C	I _D	11 8.5	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	T _A = +25 °C T _A = +70 °C	I _D	14 11	А
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _C = +25 °C T _C = +100 °C	I _D	30 20	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%	I _{DM}	90	Α		
Avalanche Current (Note 7) L = 0.1mH	las	12.7	Α		
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	8.1	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	P_{D}	0.9	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	٥	137	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	90	°C/W
Total Power Dissipation (Note 6)	P_{D}	2.4	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	В	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	35	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	P_{D}	26	W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	4.8	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV_{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25 °C	1		_	1	μΑ	V _{DS} = 30V, V _{GS} = 0V	
Zero Gate Voltage Drain Current T _J = +150 °C (Note 9)	IDSS		_	100	μΑ	VDS = 30V, VGS = 0V	
Gate-Source Leakage	I_{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		6.5	8.5	mΩ	$V_{GS} = 10V, I_D = 18A$	
Static Diani-Source On-Nesistance	R _{DS(ON)}		8	10.5	11152	$V_{GS} = 4.5V, I_D = 16A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
On State Drain Current (Note 9)	I _{D(ON)}	10	_	_	Α	$V_{DS} \leq 5V$, $V_{GS} = 4.5V$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}		2,075	4,150		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	190	380	pF		
Reverse Transfer Capacitance	C _{rss}	_	138	276		I = 1.0IVIHZ	
Gate Resistance	Rg	_	2.4	5	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	16.1	32			
Total Gate Charge (V _{GS} = 10V)	Qg		37	74	nC	V 15V L 10A	
Gate-Source Charge	Qgs	_	6.1	12	IIC	$V_{DS} = 15V, I_{D} = 18A$	
Gate-Drain Charge	Q_{gd}	_	5.9	12			
Turn-On Delay Time	t _{D(on)}	_	4.5	10			
Turn-On Rise Time	t _r		19.6	35		$V_{DS} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}		31	50	ns	$R_L = 0.83\Omega$, $R_{GEN} = 3\Omega$,	
Turn-Off Fall Time	t _f	_	10.7	21			
Reverse Recovery Time	t _{rr}	_	13.7	27	ns		
Reverse Recovery Charge	Q _{rr}	_	18.3	37	nC	-I _F =15A, di/dt=500A/μs	

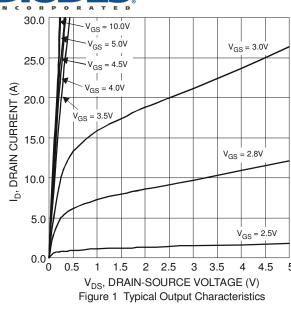
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

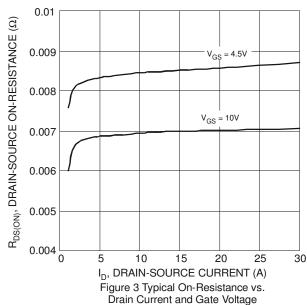
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.

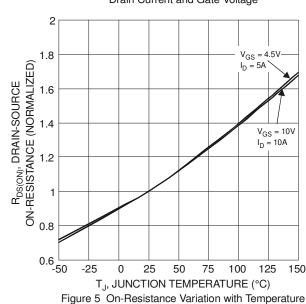
7. UIS in production with L = 1mH, TJ = +25 $^{\circ}$ C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.







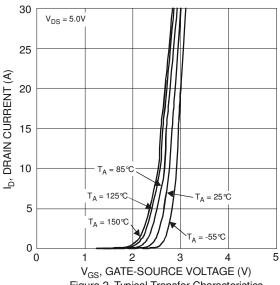


Figure 2 Typical Transfer Characteristics

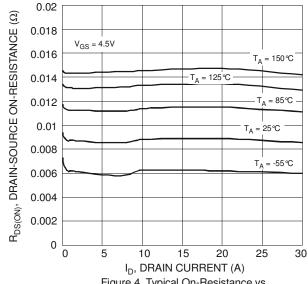


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

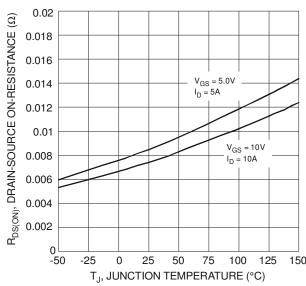
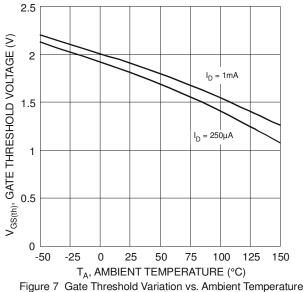
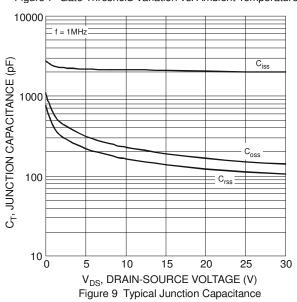
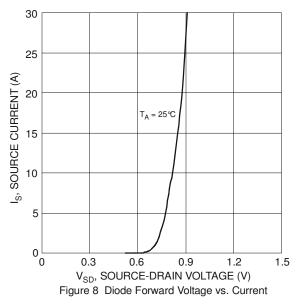


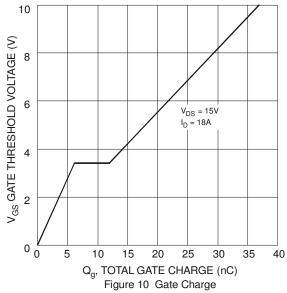
Figure 6 On-Resistance Variation with Temperature











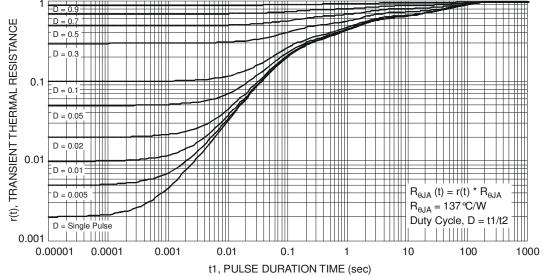
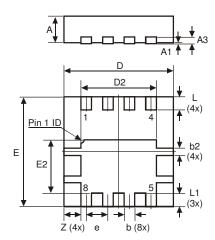


Figure 11 Transient Thermal Resistance



Package Outline Dimensions

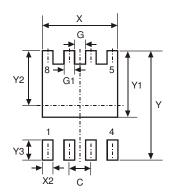
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI [®] 3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A 1	0	0.05	0.02		
A3	-	_	0.203		
b	0.27	0.37	0.32		
b2	-	_	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.420		
Υ	3.700		
Y1	2.250		
Y2	1.850		
Y3	0.700		
X	2.370		
X2	0.420		



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